



STPS3030CT/CG/CR

LOW DROP POWER SCHOTTKY RECTIFIER

MAJOR PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 15 A
V_{RRM}	30 V
$T_j(\text{max})$	150°C
$V_F(\text{max})$	0.42 V

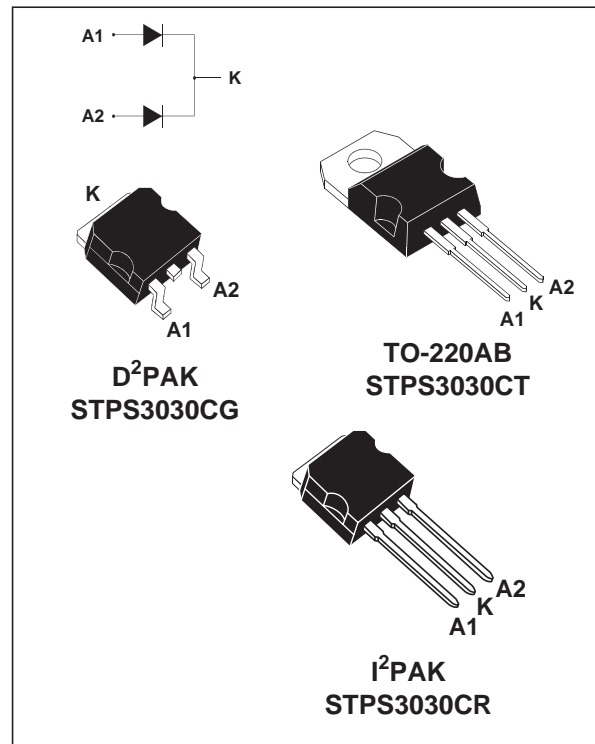
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP FOR HIGHER EFFICIENCY
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual Schottky rectifier suited for switch Mode Power Supply and high frequency DC to DC converters.

Packaged in TO-220AB, D²PAK and I²PAK, this device is intended for use in low voltage high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		30	V
$I_{F(RMS)}$	RMS forward current		30	A
$I_{F(AV)}$	Average forward current	$T_c = 135^\circ\text{C}$ $\delta = 0.5$	Per diode: 15 Per device: 30	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	250	A
I_{RRM}	Peak repetitive reverse current	$t_p = 2 \mu\text{s}$ square $F = 1\text{kHz}$	1	A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100 \mu\text{s}$ square	3	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1 \mu\text{s}$ $T_j = 25^\circ\text{C}$	4100	W
T_{stg}	Storage temperature range		- 65 to + 150	°C
T_j	Maximum operating junction temperature *		150	°C
dV/dt	Critical rate of rise of reverse voltage (rated V_R , $T_j = 25^\circ\text{C}$)		10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink

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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case TO-220AB - D ² PAK - I ² PAK	Per diode	1.2	°C/W
		Total	0.8	
$R_{th(c)}$		Coupling	0.4	°C/W

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$		0.23	1.0	mA
		$T_j = 125^\circ\text{C}$			125	180	
V_F^*	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 15\text{ A}$		0.44	0.49	V
		$T_j = 125^\circ\text{C}$	$I_F = 15\text{ A}$		0.36	0.40	
		$T_j = 25^\circ\text{C}$	$I_F = 30\text{ A}$		0.53	0.58	
		$T_j = 125^\circ\text{C}$	$I_F = 30\text{ A}$		0.49	0.53	

Pulse test : * $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.26 \times I_{F(AV)} + 0.0107 I_{F(RMS)}^2$$

Fig. 1: Conduction losses versus average current.

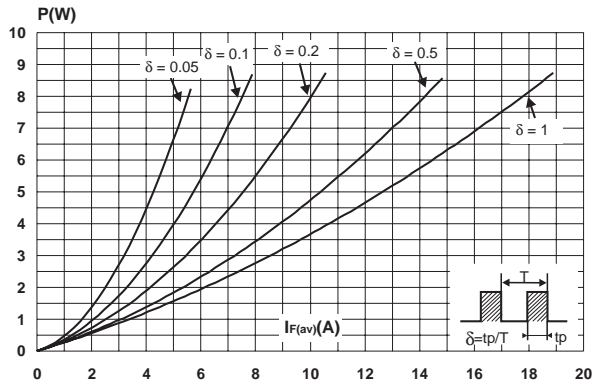


Fig. 3: Normalized avalanche power derating versus pulse duration.

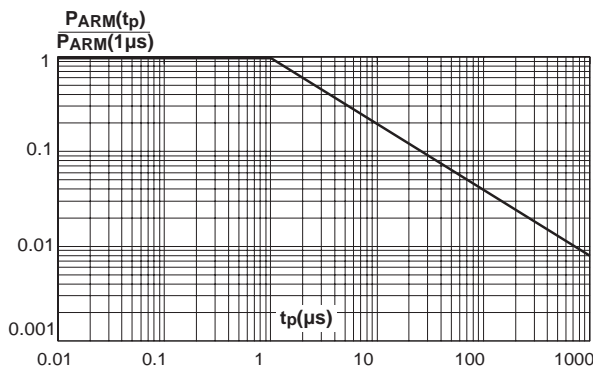


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$).

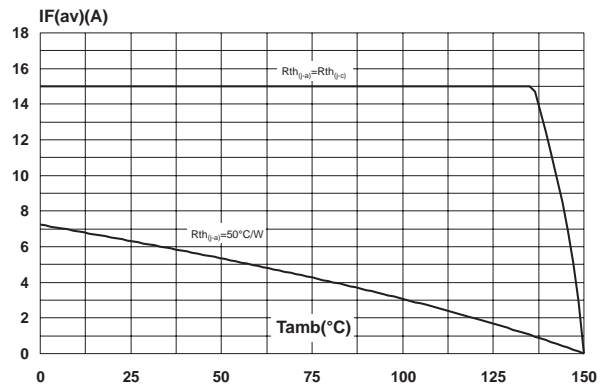


Fig. 4: Normalized avalanche power derating versus junction temperature.

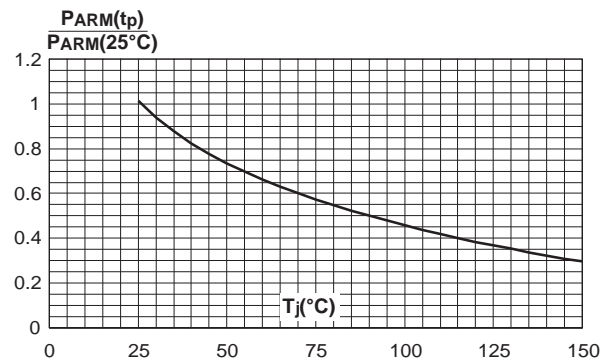


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

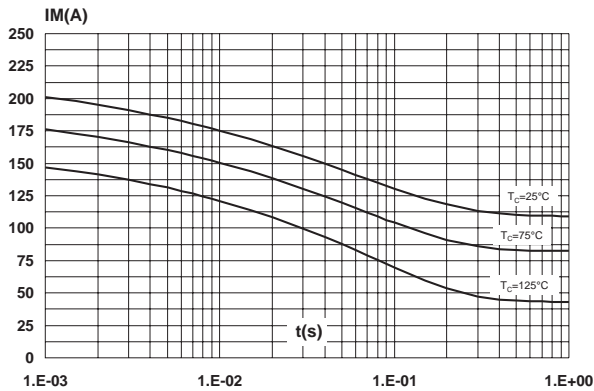


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

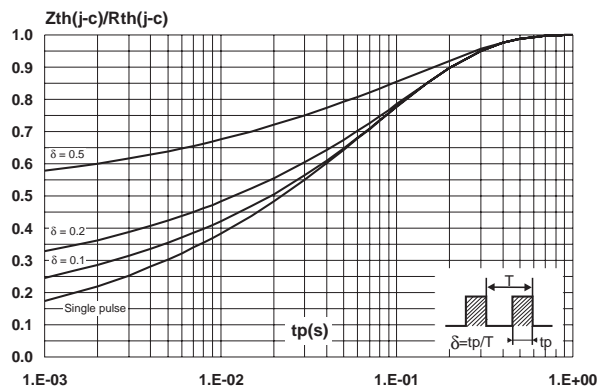


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values).

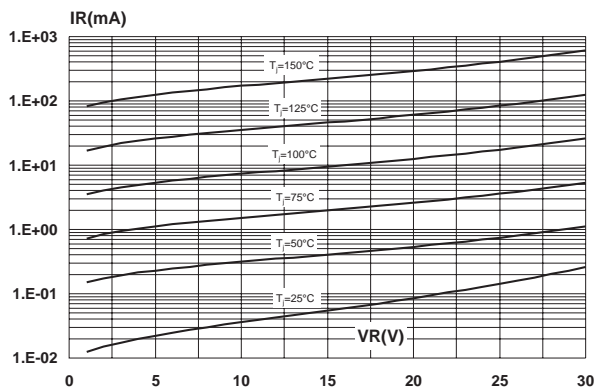


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).

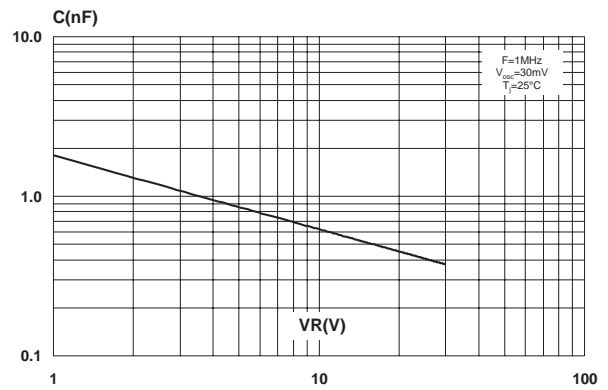


Fig. 9: Forward voltage drop versus forward current.

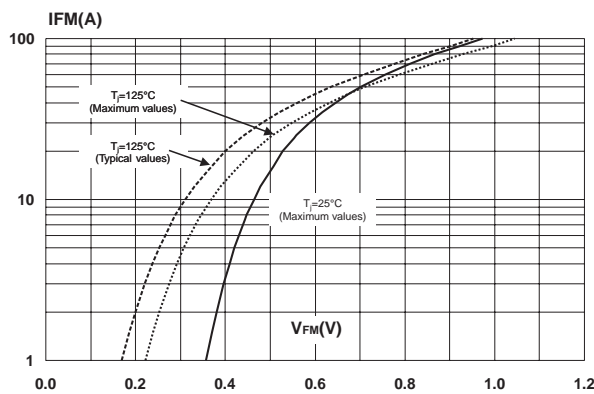
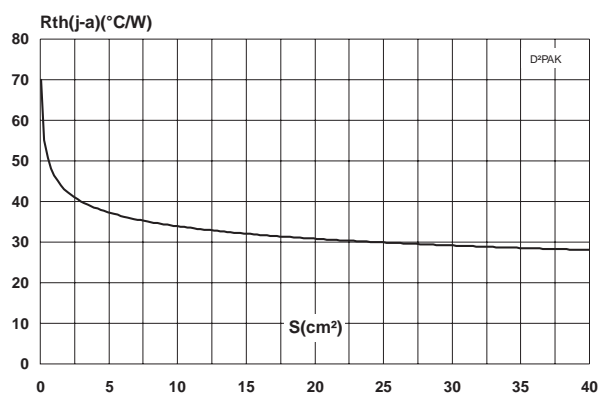
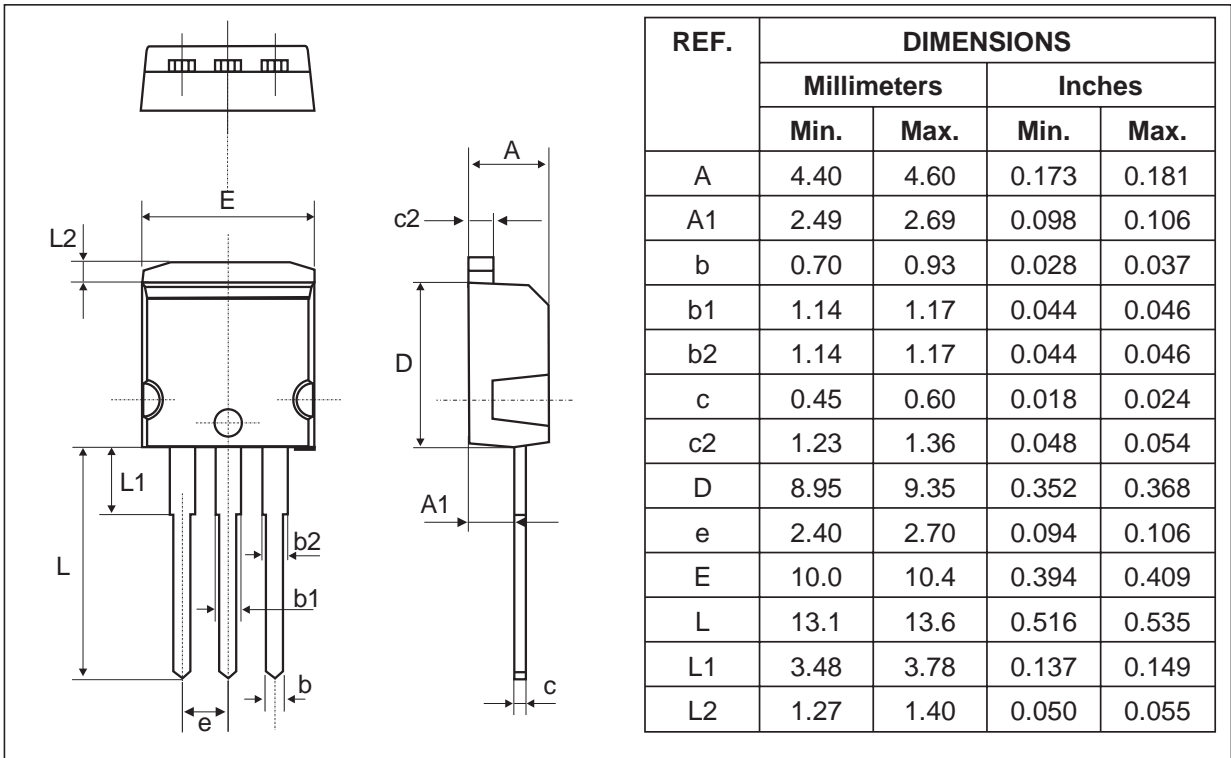


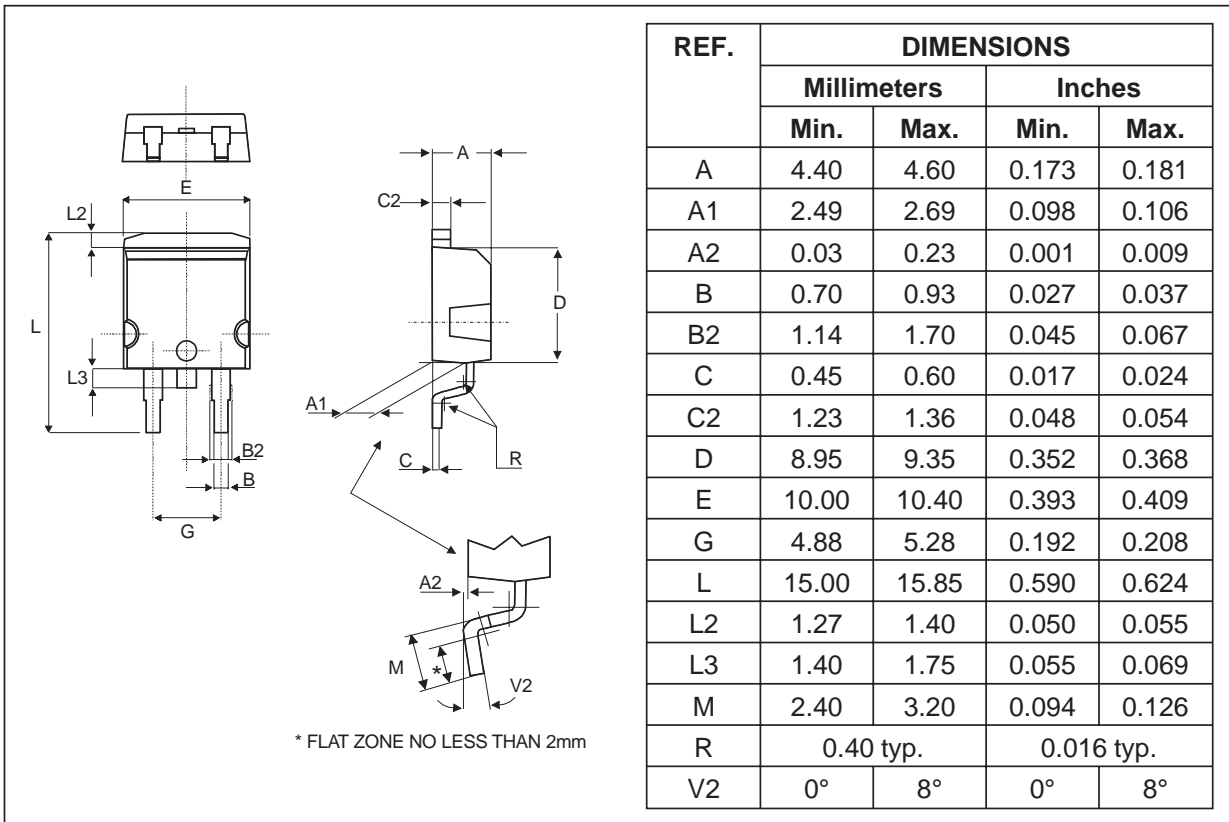
Fig. 10: Thermal resistance junction to ambient versus copper surface under tab (epoxy printed board FR4, Cu = 35μm).



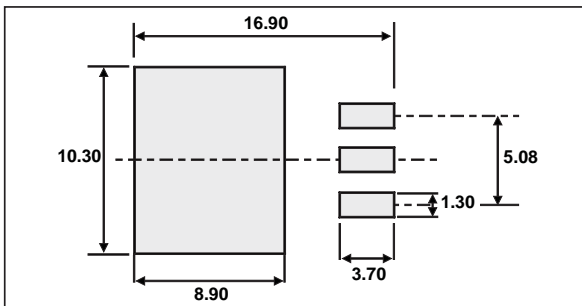
PACKAGE MECHANICAL DATA
I²PAK



PACKAGE MECHANICAL DATA
D²PAK

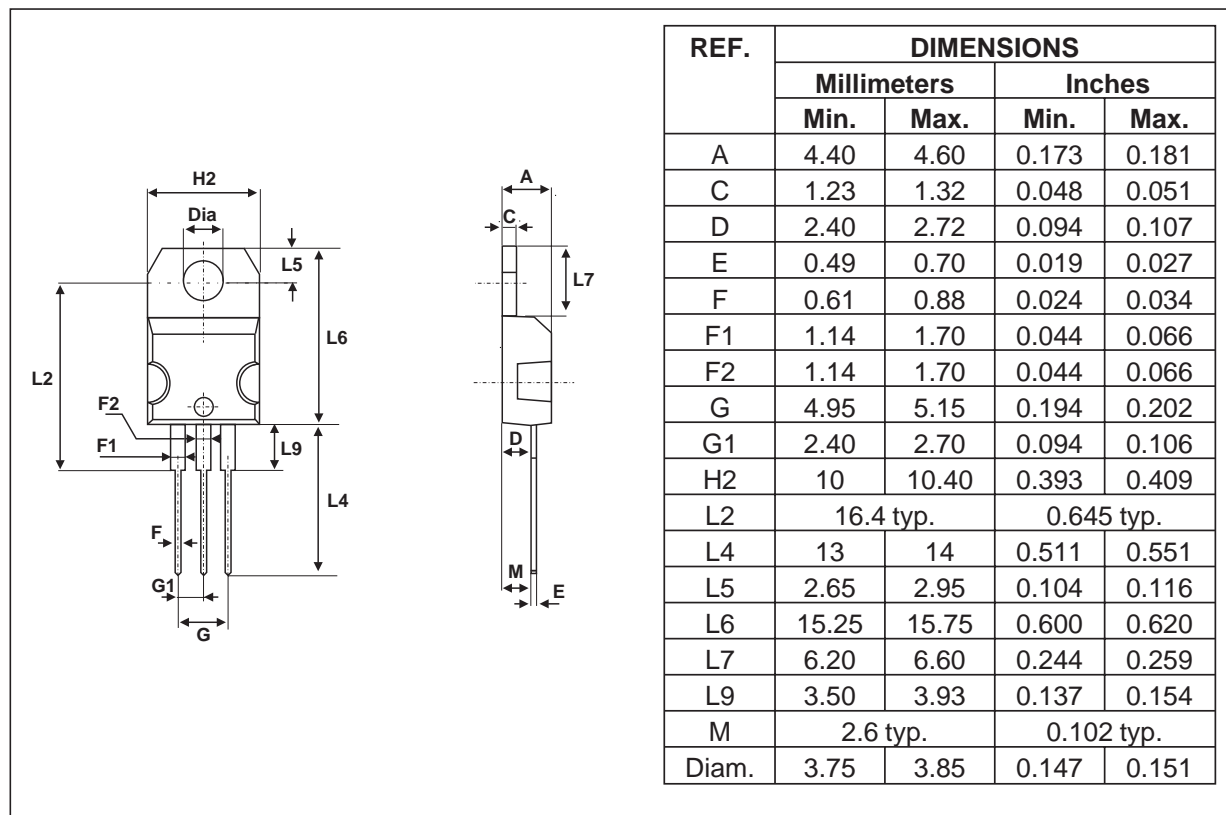


FOOTPRINT



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PACKAGE MECHANICAL DATA TO-220AB



- COOLING METHOD : C
- RECOMMENDED TORQUE VALUE : 0.55 M.N
- MAXIMUM TORQUE VALUE : 0.70 M.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS3030CT	STPS3030CT	TO-220AB	2.2 g	50	Tube
STPS3030CG	STPS3030CG	D ² PAK	1.48 g	50	Tube
STPS3030CG-TR	STPS3030CG	D ² PAK	1.48 g	1000	Tape & reel
STPS3030CR	STPS3030CR	I ² PAK	1.49 g	50	Tube

- EPOXY MEETS UL94,V0

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